

Serial No.: 10/672,093  
Group Art Unit: 2818

### AMENDMENTS TO THE SPECIFICATION

- Please amend the Cross-Reference to Related Application(s) section which begins on page 1, line 2, as follows:

#### CROSS REFERENCE TO RELATED APPLICATIONS

This is a divisional of co-pending application serial number 10/128,771, now U.S. Patent No. 6,670,241 B1, filed on April 22, 2002, which is incorporated herein by reference thereto.

- Please amend the paragraph in the specification which begins on page 8, line 1, as follows:

The wordline material 515 is patterned, etched, and stripped resulting in wordlines 518 and 519. Spacers 520 and 522 are then formed around the wordlines 518 and 519, respectively, and a on the charge trapping dielectric layer 504. A salicide layer is deposited to form salicide areas 524 and 526, respectively, on the tops of the respective wordlines 518 and 519. The locations 528 and 530 indicate where bits can be stored in the memory cell 500 and locations 532 and 534 are adjacent locations, which are independent of the memory cell 500.